

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

- Epitaxial planar Silicon diode

FEATURES

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance

APPLICATIONS

- High Conductance Ultra Fast Diode
- For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

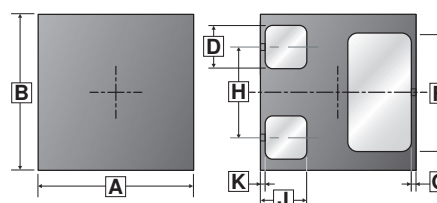
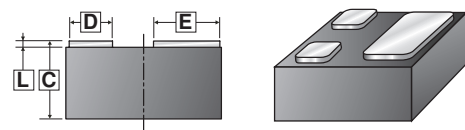
MARKING

5D

PACKAGE INFORMATION

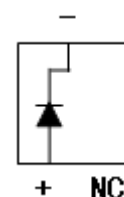
Package	MPQ	Leader Size
WBFBP-03D	5K	7 inch

WBFBP-03D



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.950	1.050	G	-	0.050
B	0.950	1.050	H	0.510	0.610
C	0.010	0.070	J	0.250	0.350
D	0.210	0.310	K	-	0.050
E	0.350 REF.		L	0.450	0.550
F	0.680 REF.				

TOP VIEW



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameters	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	100	V
Working Peak Reverse Voltage	V _{RWM}	100	V
DC Blocking Voltage	V _R	100	V
Non-Repetitive Peak reverse voltage	V _{RM}	100	V
RMS Reverse Voltage	V _{R(RMS)}	53	V
Forward Continuous Current	I _{FM}	500	mA
Average Rectified Output Current	I _o	300	mA
Power Dissipation	P _D	100	mW
Operating Junction and Storage Temperature	T _J , T _{STG}	125, -55~150	°C

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameters	Symbol	Min.	Max.	Unit	Test Conditions
Forward Voltage	V_{F1}	-	0.715	V	$I_F=1\text{mA}$
	V_{F2}	-	0.855	V	$I_F=10\text{mA}$
	V_{F3}	-	1	V	$I_F=50\text{mA}$
	V_{F4}	-	1.25	V	$I_F=150\text{mA}$
Maximum DC Reverse Current at rated DC blocking voltage	I_{R1}	-	1	μA	$V_R=75\text{V}$
	I_{R2}	-	25	nA	$V_R=20\text{V}$
Capacitance between terminals	C_T	-	2	pF	$V_R=0, f=1\text{MHz}$
Maximum Reverse Recovery Time	T_{RR}	-	4	nS	$I_F=I_R=10\text{mA}, I_{rr}=0.1I_{IR}$

CHARACTERISTIC CURVES

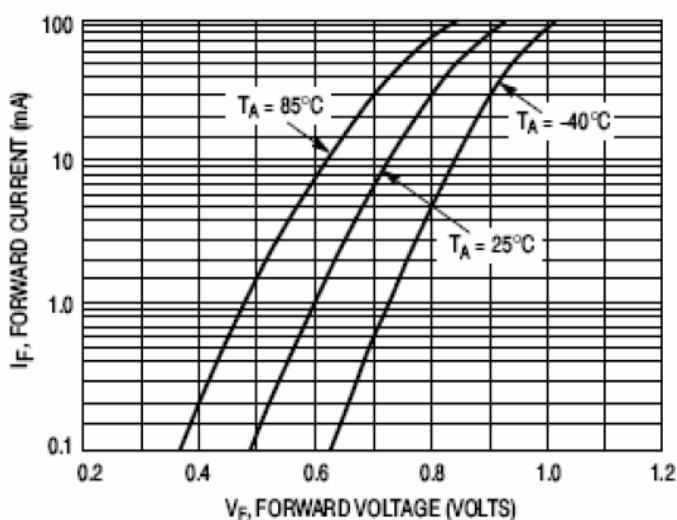


Figure 1. Forward Voltage

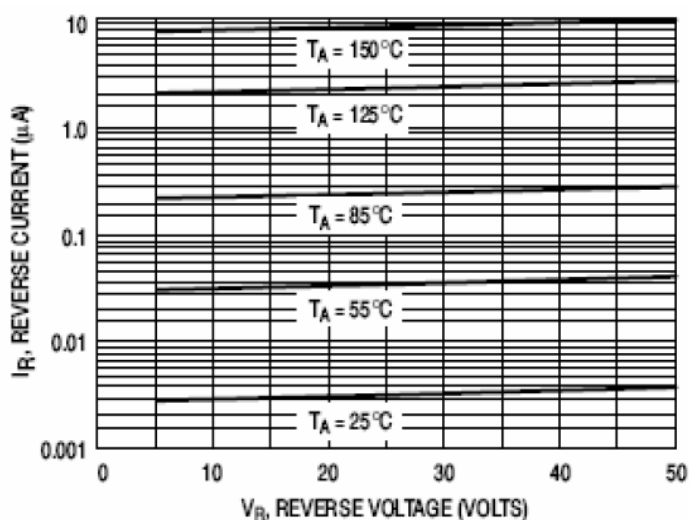


Figure 2. Leakage Current

